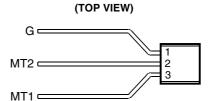


- 1.5 A RMS
- Glass Passivated Wafer
- 400 V to 600 V Off-State Voltage
- Max I<sub>GT</sub> of 10 mA
- Package Options

PACKAGE	PACKING	PART # SUFFIX		
LP	Bulk	(None)		
LP with fomed leads	Tape and Reel	R		



MDC2AA



LP PACKAGE WITH FORMED LEADS

MDC2AB

### absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT	
Repetitive peak off-state voltage (see Note 1)  TICP206D TICP206M			400 600	٧
Full-cycle RMS on-state current at (or below) 85°C case temperature (see Note 2)	T(RMS)	1.5	Α	
Peak on-state surge current full-sine-wave at (or below) 25°C case temperature (see Note 3)			10	Α
Peak on-state surge current half-sine-wave at (or below) 25°C case temperature (see Note 4)			12	Α
Peak gate current			±0.2	Α
Average gate power dissipation at (or below) 85°C case temperature (see Note 5)	P <sub>G(AV)</sub>	0.3	W	
Operating case temperature range			-40 to +110	°C
Storage temperature range		T <sub>stg</sub>	-40 to +125	°C
Lead temperature 1.6 mm from case for 10 seconds			230	°C

- NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
  - 2. This value applies for 50-Hz full-sine- wave operation with resistive load. Above 85°C derate linearly to 110°C case temperature at the rate of 60 mA/°C.
  - 3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
  - 4. This value applies for one 50-Hz half-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
  - 5. This value applies for a maximum averaging time of 20 ms.

## electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
I <sub>DRM</sub>	Repetitive peak off- state current	V <sub>D</sub> = rated V <sub>DRM</sub>	I <sub>G</sub> = 0				±20	μА
		V <sub>supply</sub> = +12 V†	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs			8	mA
la-	Gate trigger	$V_{\text{supply}} = +12 \text{ V}\dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$			-8	
IGT	current	$V_{\text{supply}} = -12 \text{ V}\dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$			-8	ША
		$V_{\text{supply}} = -12 \text{ V}\dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$			10	
		$V_{\text{supply}} = +12 \text{ V}\dagger$	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs			2.5	V
V <sub>GT</sub>	Gate trigger	$V_{\text{supply}} = +12 \text{ V}\dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$			-2.5	
	voltage	$V_{\text{supply}} = -12 \text{ V}\dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$			-2.5	V
		$V_{\text{supply}} = -12 \text{ V}\dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$			2.5	

<sup>†</sup> All voltages are with respect to Main Terminal 1.

## PRODUCT INFORMATION



## electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

	PARAMETER TEST CONDITIONS			MIN	TYP	MAX	UNIT	
V <sub>T</sub>	On-state voltage	I <sub>T</sub> = ±1 A	I <sub>G</sub> = 50 mA	(see Note 6)			±2.2	V
I <sub>H</sub>	Holding current	$V_{\text{supply}} = +12 \text{ V}^{\dagger}$ $V_{\text{supply}} = -12 \text{ V}^{\dagger}$	I <sub>G</sub> = 0 I <sub>G</sub> = 0	Init' $I_{TM} = 100 \text{ mA}$ Init' $I_{TM} = -100 \text{ mA}$			30 -30	mA
IL	Latching current	$V_{\text{supply}} = +12 \text{ V}^{\dagger}$ $V_{\text{supply}} = -12 \text{ V}^{\dagger}$	(see Note 7)				40 -40	mA

<sup>†</sup> All voltages are with respect to Main Terminal 1.

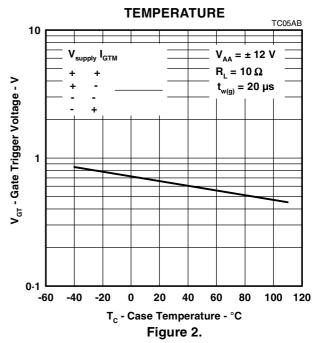
# TYPICAL CHARACTERISTICS

#### GATE TRIGGER CURRENT

# VS **TEMPERATURE** TC05AA 100 $V_{AA} = \pm 12 \text{ V}$ supply I<sub>GTM</sub> $R_L = 10 \Omega$ $t_{w(g)} = 20 \ \mu s$ I<sub>GT</sub> - Gate Trigger Current - mA 10 -60 -40 -20 20 40 60 80 100 120 T<sub>c</sub> - Case Temperature - °C Figure 1.

# **GATE TRIGGER VOLTAGE**

vs

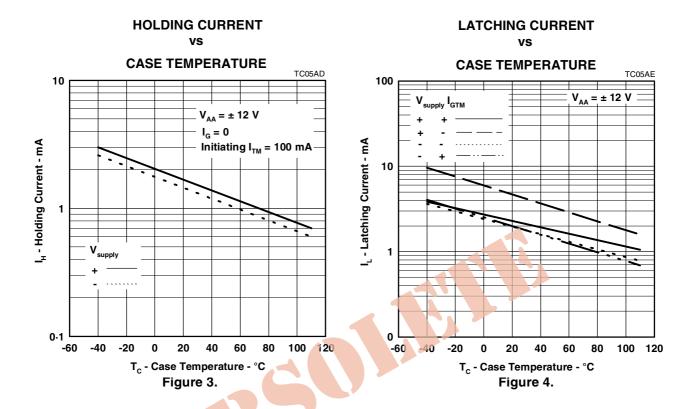


#### PRODUCT INFORMATION

NOTES: 6. This parameter must be measured using pulse techniques, t<sub>p</sub> = ≤ 1 ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

<sup>7.</sup> The triacs are triggered by a 15-V (open circuit amplitude) pulse supplied by a generator with the following characteristics:  $R_G = 100 \ \Omega$ ,  $t_{p(g)} = 20 \ \mu s$ ,  $t_r = \le 15 \ ns$ ,  $f = 1 \ kHz$ .

#### **TYPICAL CHARACTERISTICS**



# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

# Bourns:

TICP206D-R-S TICP206D-S TICP206M-S